

F7755-VB Datasheet

Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
- 30	0.036 at V _{GS} = - 10 V	- 5.2	
- 30	0.055 at V _{GS} = - 4.5 V	- 4.2	

FEATURES

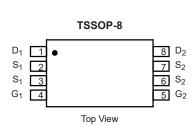
- · Halogen-free
- Trench Power MOSFETs

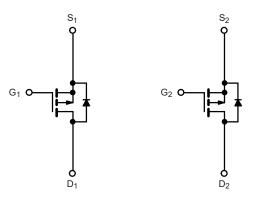


RoHS COMPLIANT

APPLICATIONS

- · Load Switch
- · Battery Switch





P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise r	noted		_
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V _{GS}	± 20		V
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	- 5.2	- 4.1	Δ.
	T _A = 70 °C		- 4.2	- 3.6	
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.0	- 0.70	
Maximum Power Dissipation ^a	T _A = 25 °C	Б	1.14	0.83	W
	T _A = 70 °C	P_{D}	0.73	0.53	
Operating Junction and Storage Temperature Range		T _J , T _{sta}	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana landina ta Ambianta	t ≤ 10 s	R _{thJA}	86	110	
Maximum Junction-to-Ambient ^a	Steady State		124	150	°C/W
Maximum Junction-to-Foot	Steady State	R _{thJF}	52	65	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

服务热线:400-655-8788

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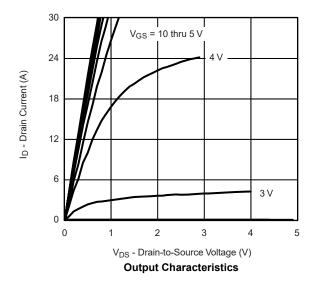
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zana Cata Valta da Dunia Comuna		V _{DS} = - 30 V, V _{GS} = 0 V			- 1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α
Drain-Source On-State Resistance ^a	Б	$V_{GS} = -10 \text{ V}, I_D = -4.7 \text{ A}$	V _{GS} = - 10 V, I _D = - 4.7 A			Ω
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.8 A		0.055		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 4.7 A		14		S
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.74	- 1.1	V
Dynamic ^b	•			'		
Total Gate Charge	Q_g			13	20	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.7 \text{ A}$		3		nC
Gate-Drain Charge	Q _{gd}			5.8		
Gate Resistance	R_g	f = 1.0 MHz		4.6		Ω
Turn-On Delay Time	t _{d(on)}			13	20	
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	22	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, V_{GEN} = - 10 V, R_G = 6 Ω		52	80	ns
Fall Time	t _f			26	40	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.0 A, dI/dt = 100 A/μs		40	60	

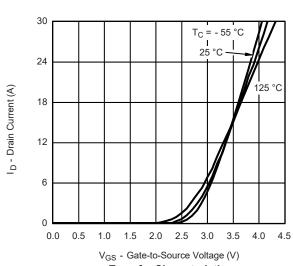
Notes:

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

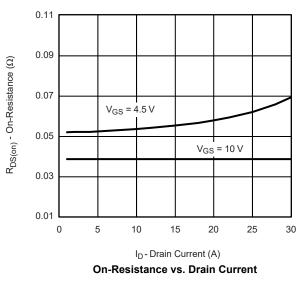


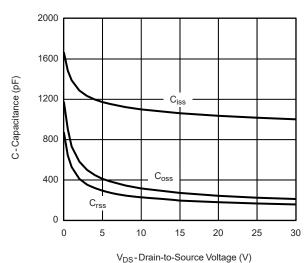


Transfer Characteristics

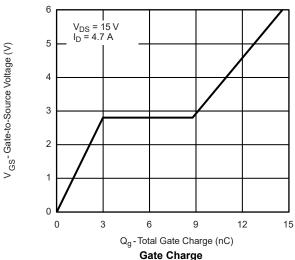


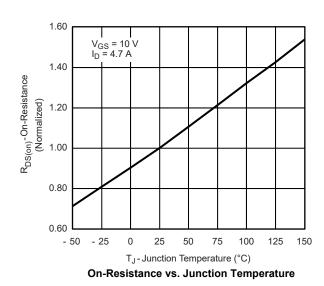
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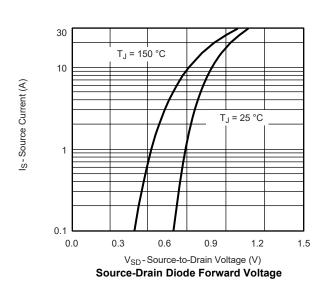


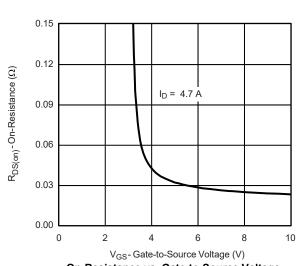


Capacitance







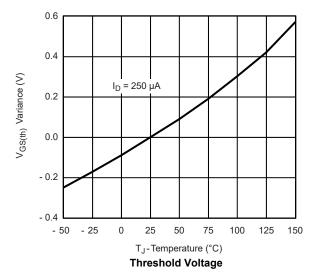


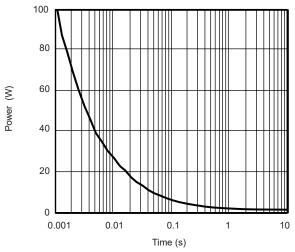
On-Resistance vs. Gate-to-Source Voltage

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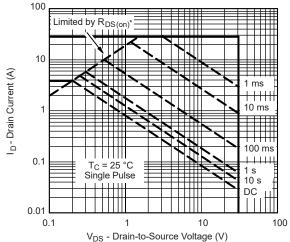


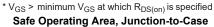
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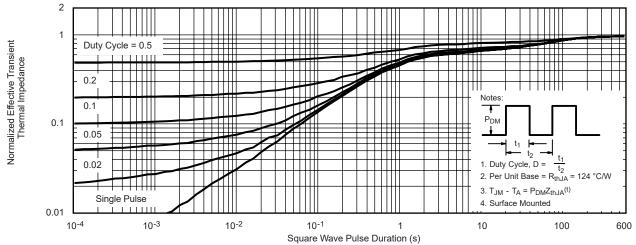




Single Pulse Power, Junction-to-Ambient



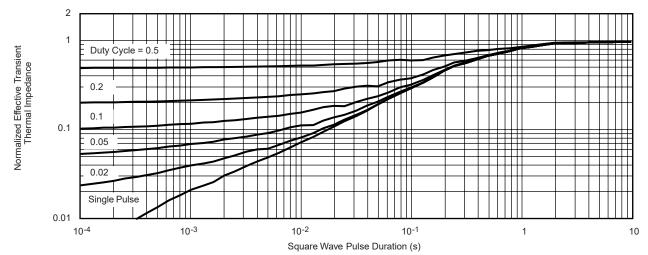




Normalized Thermal Transient Impedance, Junction-to-Ambient



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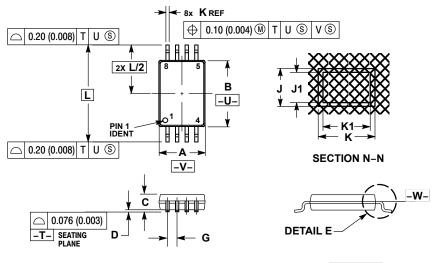


Normalized Thermal Transient Impedance, Junction-to-Foot



TSSOP-8





	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	4.30	4.50	0.169	0.177
С		1.10		0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65 BSC		0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252	
M	0°	8°	0	8 °

N 🚤	0.25 (0.010)
N.	→ M → ↓
≠ F	1

DETAIL E



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